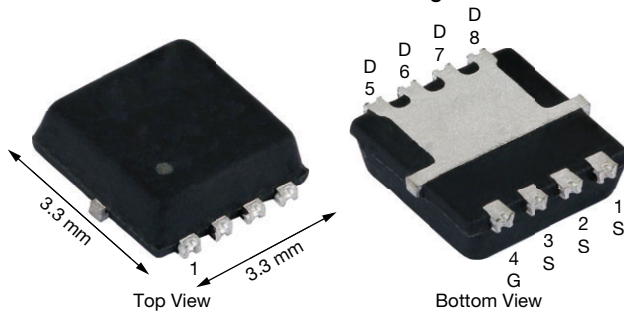


## Automotive N-Channel 60 V (D-S) 175 °C MOSFET

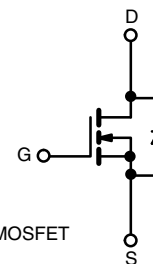
**PowerPAK® 1212-8W Single**

**FEATURES**

- TrenchFET® power MOSFET
- Low thermal resistance PowerPAK® 1212-8 package with 1.07 mm profile
- PWM optimized
- 100 %  $R_{\theta}$  and UIS tested
- AEC-Q101 qualified
- Wettable flank terminals
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

 AUTOMOTIVE  
GRADE

**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**
**Marking Code:** Q037

PRODUCT SUMMARY	
$V_{DS}$ (V)	60
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.023
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.028
$I_D$ (A)	18
Configuration	Single
Package	PowerPAK 1212-8W



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		$V_{DS}$	60	V
Gate-source voltage		$V_{GS}$	$\pm 20$	
Continuous drain current <sup>a</sup>	$T_C = 25$ °C	$I_D$	18	A
	$T_C = 125$ °C		18	
Continuous source current (diode conduction) <sup>a</sup>		$I_S$	18	
Pulsed drain current <sup>b</sup>		$I_{DM}$	72	
Single pulse avalanche current	L = 0.1 mH	$I_{AS}$	20	mJ
Single pulse avalanche energy		$E_{AS}$	16	
Maximum power dissipation <sup>b</sup>	$T_C = 25$ °C	$P_D$	62	W
	$T_C = 125$ °C		20	
Operating junction and storage temperature range		$T_J, T_{stg}$	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>d</sup>			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	$R_{thJA}$	81	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.4	

**Notes**

- Package limited
- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %
- When mounted on 1" square PCB (FR4 material)
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		1.5	2	2.5	
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	20	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 8.7\text{ A}$	-	0.016	0.023	$\Omega$
		$V_{GS} = 10\text{ V}$	$I_D = 8.7\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	0.039	
		$V_{GS} = 10\text{ V}$	$I_D = 8.7\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	0.050	
		$V_{GS} = 4.5\text{ V}$	$I_D = 8.7\text{ A}$	-	0.019	0.028	
Forward transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 8.7\text{ A}$		-	50	-	S
<b>Dynamic <sup>b</sup></b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 30\text{ V}$ , $f = 1\text{ MHz}$	-	1275	1590	$\text{pF}$
Output capacitance	$C_{oss}$			-	112	140	
Reverse transfer capacitance	$C_{rss}$			-	42	52	
Total gate charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}$ , $I_D = 8.7\text{ A}$	-	19	25	$\text{nC}$
Gate-source charge <sup>c</sup>	$Q_{gs}$			-	2.6	-	
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	3.6	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$		0.6	1.12	1.6	$\Omega$
Turn-on delay time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}$ , $R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$		-	8	10	$\text{ns}$
Rise time <sup>c</sup>	$t_r$			-	13	16	
Turn-off delay time <sup>c</sup>	$t_{d(off)}$			-	22	26	
Fall time <sup>c</sup>	$t_f$			-	15	18	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>							
Pulsed current <sup>a</sup>	$I_{SM}$			-	-	72	A
Forward voltage	$V_{SD}$	$I_F = 8.7\text{ A}$ , $V_{GS} = 0\text{ V}$		-	0.8	1.2	V

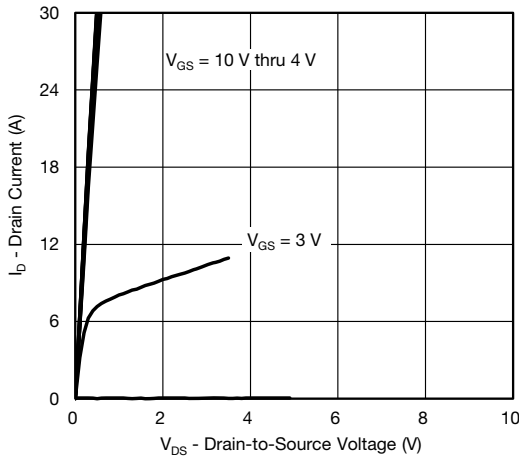
**Notes**

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- Guaranteed by design, not subject to production testing
- Independent of operating temperature

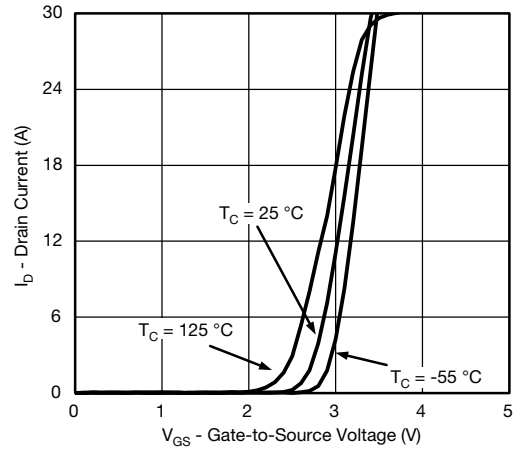
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.



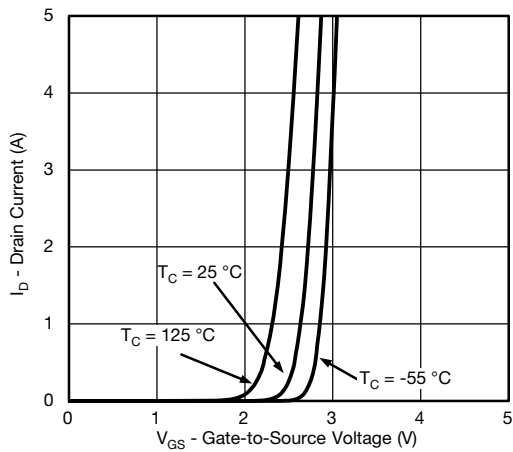
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



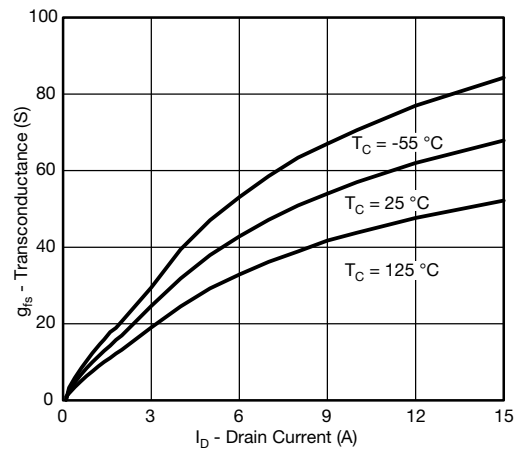
Output Characteristics



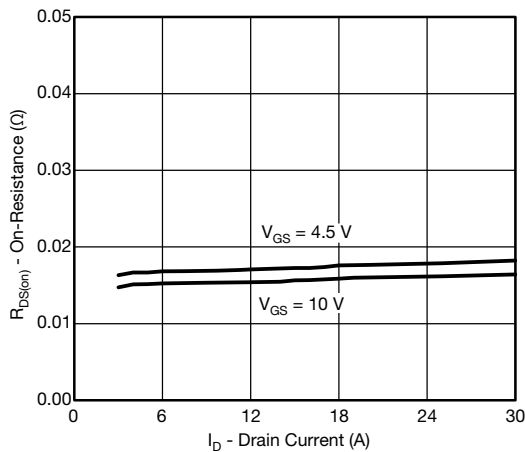
Transfer Characteristics



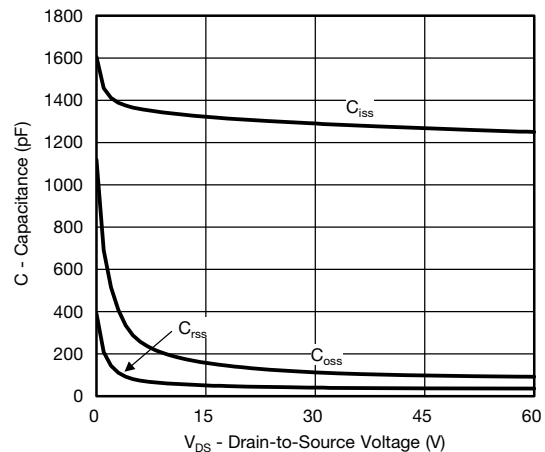
Transfer Characteristics



Transconductance



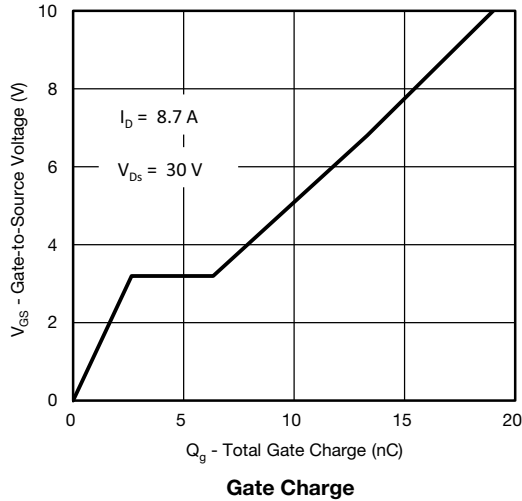
On-Resistance vs. Drain Current



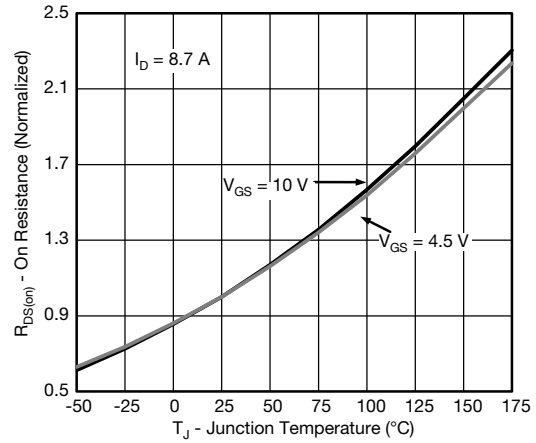
Capacitance



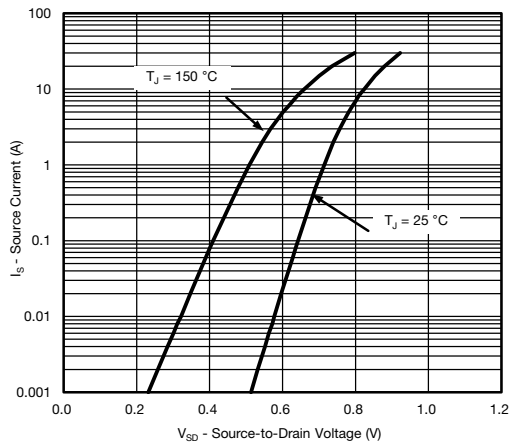
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



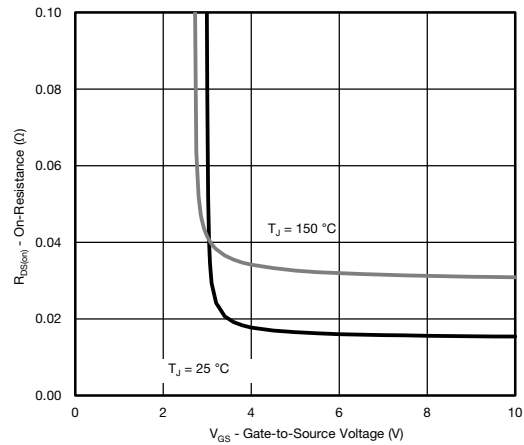
Gate Charge



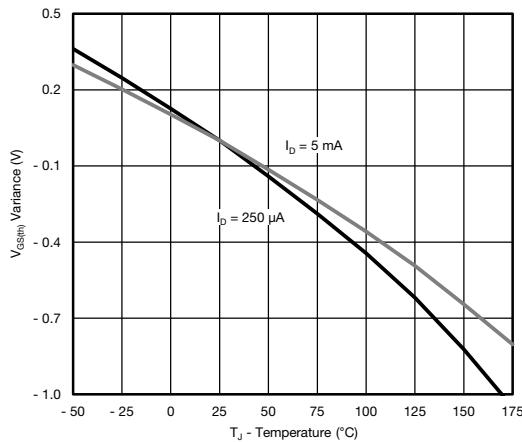
On-Resistance vs. Junction Temperature



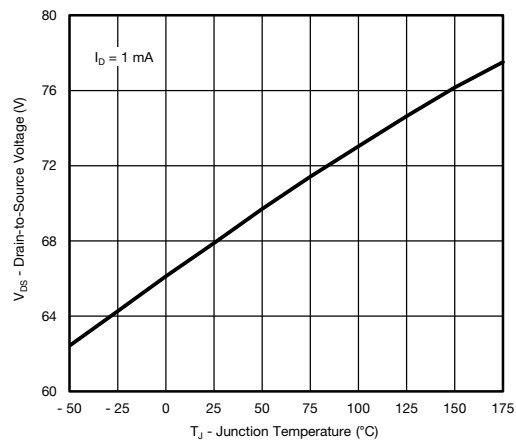
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



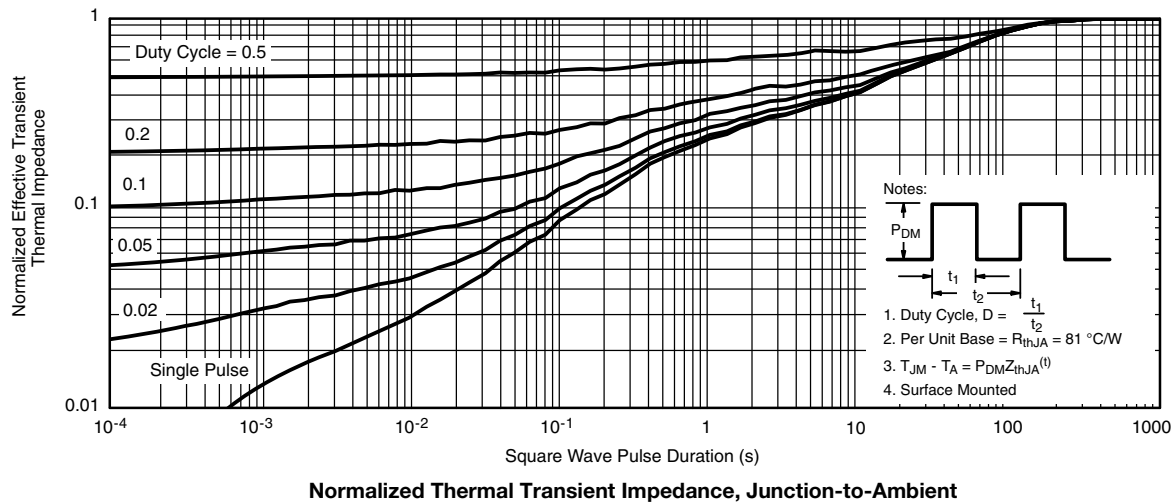
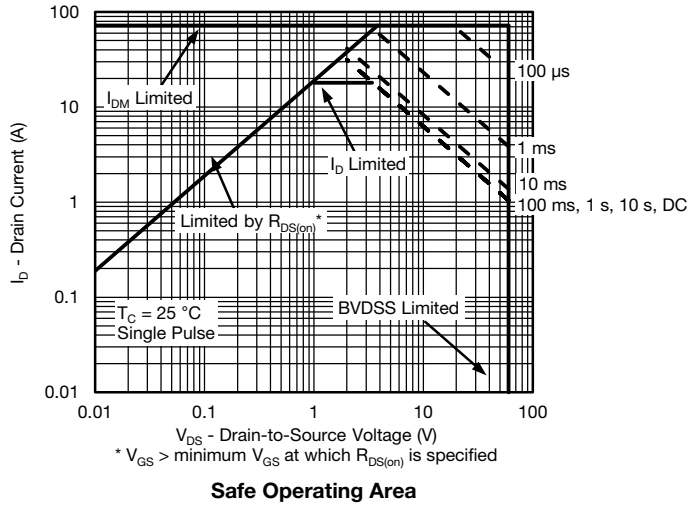
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

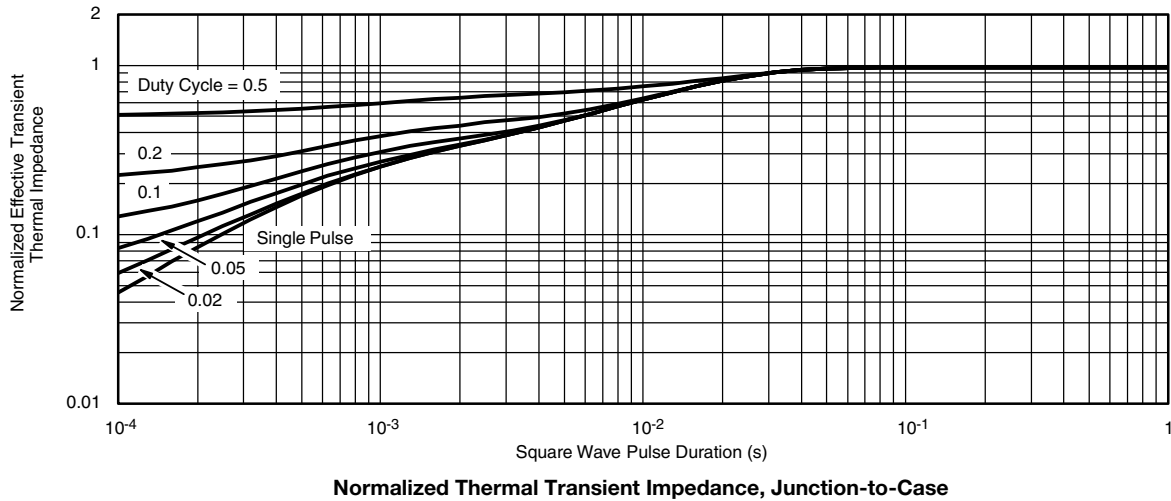


**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)





**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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